# 10V Drive Nch MOSFET

# **R5011ANX**

#### Structure

Silicon N-channel MOSFET

#### Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (VGSS) guaranteed to be  $\pm 30$ V.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.

#### Applications

Switching

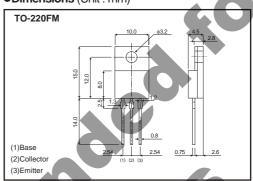
#### Packaging specifications

	Package	Bulk
Type	Code	
	Basic ordering unit (pieces)	500
R5011	ANX	0

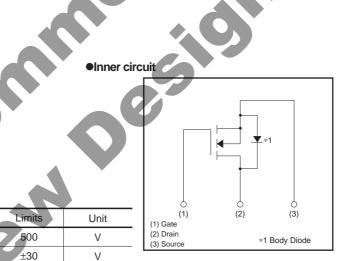
#### ● Absolute maximum ratings (Ta=25°C)

Parameter	Symbo	ı	Limits	Unit	
Drain-source voltage	VDSS		500	V	
Gate-source voltage	Vgss		±30	V	
Drois	Continuous	l <sub>D</sub>	*3	±11	А
Drain current	Pulsed	IDP	*1	±44	А
Source current	Continuous	ls	*3	11	А
(Body Diode)	Pulsed	Isp	*1	44	А
Avalanche Current	las	*2	5.5	А	
Avalanche Energy	Eas	*2	8.1	mJ	
Total power dissipation	PD		50	W	
Channel temperature	Tch		150	°C	
Range of storage tem	Tstg		-55 to +150	°C	

#### ●Dimensions (Unit:mm)







<sup>\*1</sup> Pw≤10 $\mu$ s, Duty cycle≤1% \*2 L $\stackrel{.}{=}$  500 $\mu$ H, V $_{DD}$ =50V, Rg=25 $\Omega$ , Starting, Tch=25°C \*3 Limited only by maximum tempterature allowed

#### Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	2.5	°C/W

#### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	_	±100	nA	Vgs=±30V, Vds=0V
Drain-source breakdown voltage	V(BR)DSS	500	_	_	V	In=1mA, Vgs=0V
Zero gate voltage drain current	IDSS	_	_	100	μΑ	Vps=500V, Vgs=0V
Gate threshold voltage	VGS(th)	2.5	_	4.5	V	VDS=10V, ID=1mA
Static drain-source on-state resistance	RDS(on)*	_	0.38	0.5	Ω	In=5.5A, Vgs=10V
Forward transfer admittance	Yfs   *	3.5	_	-	S	ID=5.5A, VDS=10V
Input capacitance	Ciss	_	1000	-	pF	VDS=25V
Output capacitance	Coss	_	400	-	pF	Vgs=0V
Reverse transfer capacitance	Crss	_	35	-	pF	f=1MHz
Turn-on delay time	td(on) *	_	26	-	ns .	lb=5.5A, Vdd≒250V
Rise time	tr *	_	28	-	ns	Vgs=10V
Turn-off delay time	td(off) *	_	75	-	ns	RL=45.5Ω
Fall time	t <sub>f</sub> *	_	30	-	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	_	30		nC	V <sub>DD</sub> ≒250V
Gate-source charge	Qgs *	_	7	7	nC	Ip=11A Vgs=10V
Gate-drain charge	Qgd *	-	12	Y	nC	$R_L=22.7\Omega/R_G=10\Omega$

<sup>\*</sup> Pulsed

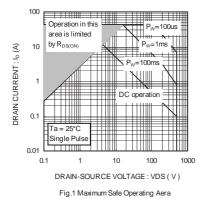
### ●Body diode characteristics (Source-drain) (Ta=25°C)

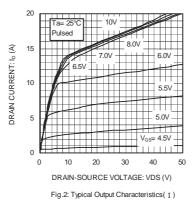
Parameter	Symbol Min.	Тур.	Max.	Unit		Conditions
Forward voltage	Vsp* -	_	1.5	V	Is= 11A	v. Vgs=0V

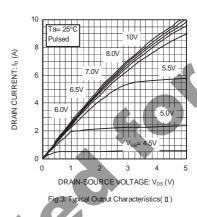
<sup>1</sup> OIWa

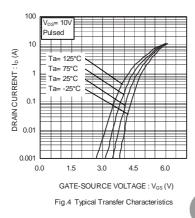


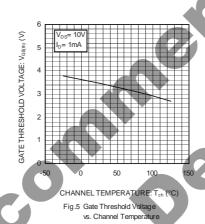
#### Electrical characteristic curves

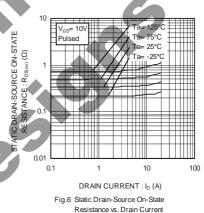


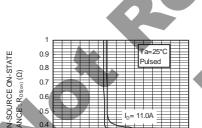


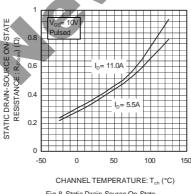


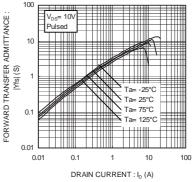








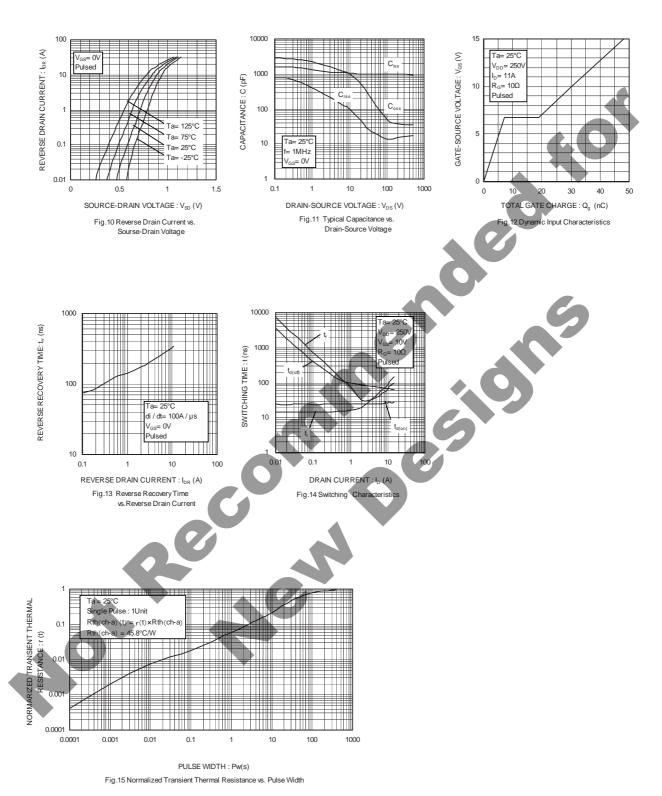




 $\mathsf{GATE}\text{-}\mathsf{SOURCE}\,\,\mathsf{VOLTAGE}:\mathsf{V}_{\mathsf{GS}}\,(\mathsf{V})$ Fig.7 Static Drain-Source On-State Resistance vs. Gate Source Voltage

Fig.8 Static Drain-Source On-State Resistance vs. Channel Temperature

Fig.9 Forward Transfer Admittance vs. Drain Current



#### Switching characteristics measurement circuit

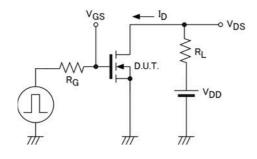


Fig.1-1 Switching Time Measurement Circuit

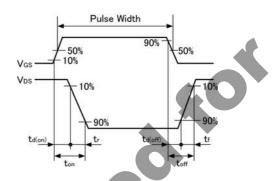


Fig.1-2 Switching Waveforms

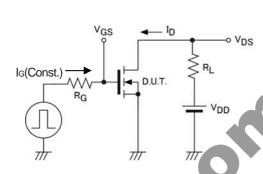


Fig.2-1 Gate Charge Measurement Circuit

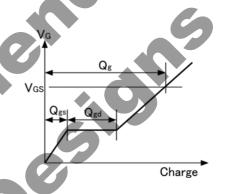


Fig.2-2 Gate Charge Waveform

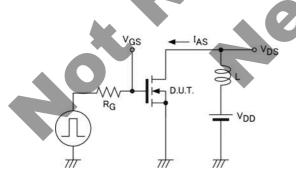


Fig.3-1 Avalanche Measurement Circuit

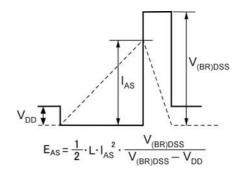


Fig.3-2 Avalanche Waveform

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